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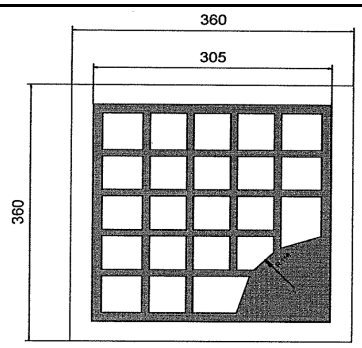
Data Sheet

LED Chip Infrared EOLC-1650-17-1

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	InGaAs/InP, MQW	P (anode) up



typ. dimensions (µm)

typ. thickness: 260 µm

anode: gold alloy, thickness 1.5 µm

cathode: gold alloy, thickness 0.5 µm

Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			100	mA
Peak forward current	$t_p \leq$ 50 µs, t_p/T=½	I_{FM}			200	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		0.7	0.95	V
Forward voltage	I_F=100 mA	V_F		0.8	1	V
Reverse voltage	I_R=100 µA	V_R	5			V
Radiant power*	I_F=20 mA	Φ_e	0.55	0.75		mW
Radiant power*	I_F=100 mA	Φ_e	1.7	2.5		mW
Peak wavelength	I_F=20 mA	λ_p	1610	1650	1690	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		100		nm
Switching times	I_F=20 mA	t_r, t_f		25; 45		ns

[1] Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 100

RoHS COMPLIANT Pb-Free